

UTC UNISONIC TECHNOLOGIES CO., LTD

8050S

NPN SILICON TRANSISTOR

LOW VOLTAGE HIGH **CURRENT SMALL SIGNAL** NPN TRANSISTOR

DESCRIPTION

The UTC 8050S is a low voltage high current small signal NPN transistor, designed for Class B push-pull audio amplifier and general purpose applications.

FEATURES

*Collector current up to 700mA *Collector-Emitter voltage up to 20V *Complementary to UTC 8550S

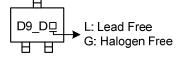
SOT-23 1 TO-92

ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Decking	
Normal	Lead Free Plating	Halogen-Free	Package	1	2	3	Packing
8050S-x-AE3-R	8050SL-x-AE3-R	8050SG-x-AE3-R	SOT-23	ш	В	С	Tape Reel
8050S-x-T92-B	8050SL-x-T92-B	8050SG-x-T92-B	TO-92	Е	С	В	Tape Box
8050S-x-T92-K	8050SL-x-T92-K	8050SG-x-T92-K	TO-92	Е	С	В	Bulk

(3)Rank (3) x: refer to Classification of h _{FE2} (4)Lead Free (4) G: Halogen Free, L: Lead Free, Blank: Pb/Sn			
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MARKING (For SOT-23 Package)



■ **ABSOLUTE MAXIMUM RATING** (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	30	V
Collector-Emitter Voltage		V _{CEO}	20	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		Ιc	700	mA
Collector Dissipation(Ta=25°C)	SOT-23	D	350	mW
	TO-92	Pc	1	W
Junction Temperature		ТJ	+150	°C
Storage Temperature		T _{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$	30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I _C = 1mA, I _B = 0	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E = 100μA, I _C =0	5			V
Collector Cut-Off Current	I _{CBO}	$V_{CB} = 30V, I_E = 0$			1	uA
Emitter Cut-Off Current	I _{EBO}	$V_{EB} = 5V, I_{C} = 0$			100	nA
	h _{FE1}	$V_{CE} = 1V$, $I_C = 1mA$	100		400	
DC Current Gain(note)	h _{FE2}	V _{CE} = 1V, I _C = 150 mA	120			
	h _{FE3}	V _{CE} = 1V, I _C = 500mA	40			
Collector-Emitter Saturation Voltage	V _{CEO(SAT)}	I _C = 500mA, I _B = 50mA			0.5	V
Base-Emitter Saturation Voltage	V _{BEO(SAT)}	I _C = 500mA, I _B = 50mA			1.2	V
Base-Emitter Saturation Voltage	V _{BEO(SAT)}	V _{CE} = 1V, I _C = 10mA			1.0	V
Current Gain Bandwidth Product	f⊤	V _{CE} = 10V, I _C = 50mA	100			MHz
Output Capacitance	Cob	V _{CB} = 10V, I _E = 0, f = 1MHz		9.0		pF

CLASSIFICATION OF h_{FE2}

RANK	С	D	E
RANGE	120-200	160-300	280-400

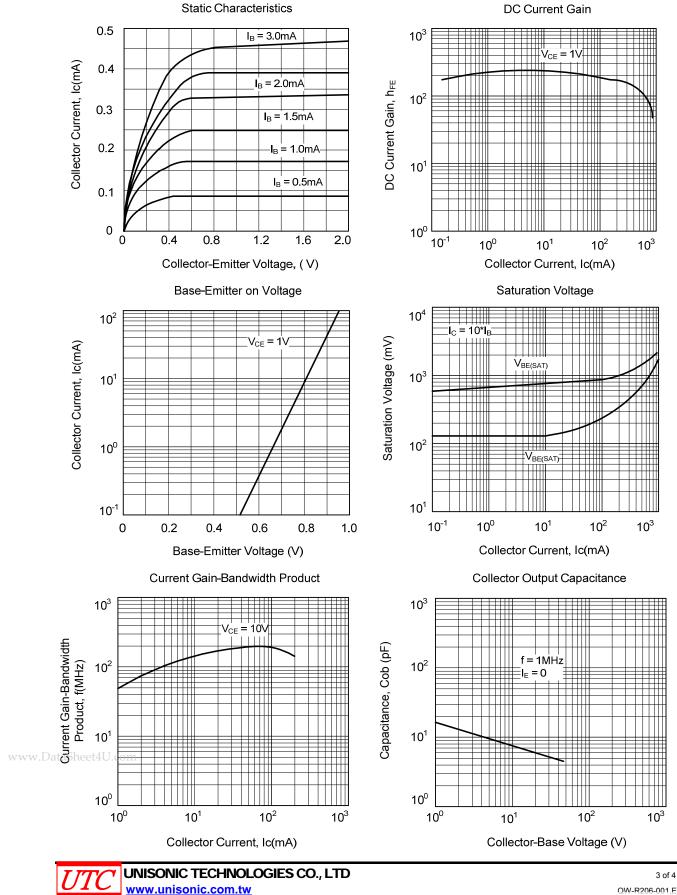
www.DataSheet4U.com



8050S

NPN SILICON TRANSISTOR

TYPICAL CHARACTERISTICS



www.Da

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